

Performance of irradiated FBK 3D sensors for the ATLAS ITk pixel detector

Thursday 18 February 2021 14:00 (20 minutes)

3D pixel sensors will be used for the innermost layer (L0) of the ATLAS ITk detector at High Luminosity LHC. The pixel size will be either $25\ \mu\text{m} \times 100\ \mu\text{m}$ (barrel, central part of L0) or $50\ \mu\text{m} \times 50\ \mu\text{m}$ (endcap, lateral rings). Sensor wafers with $150\ \mu\text{m}$ active thickness have been produced by FBK in collaboration with INFN. Several sensors were bump bonded to RD53A read-out chips at Leonardo and tested in laboratory and at DESY beam line. In this talk, we report on the test beam characterization in terms of hit efficiency and charge collection of two modules ($25\ \mu\text{m} \times 100\ \mu\text{m}$ and $50\ \mu\text{m} \times 50\ \mu\text{m}$) irradiated with 27 MeV protons up to a fluence of $1.0 \times 10^{16}\ 1\ \text{MeV}\ n_{eq}\ \text{cm}^{-2}$. Moreover, leakage current and power dissipation of 3D diodes after 1.0 and $1.5 \times 10^{16}\ 1\ \text{MeV}\ n_{eq}\ \text{cm}^{-2}$ irradiation with neutrons is shown. Finally, the preparation work for the assembly of endcap L0 modules in INFN Genoa is presented.

Primary author: LAPERTOSA, Alessandro (INFN e Universita Genova (IT))

Co-authors: VANNOLI, Leonardo (INFN e Universita Genova (IT)); GEMME, Claudia (INFN Genova (IT)); Prof. DALLA BETTA, Gian-Franco (INFN and University of Trento); ALIMONTI, Gianluca (Università degli Studi e INFN Milano (IT)); GARIANO, Giuseppe (INFN e Universita Genova (IT)); ROVANI, alessandro (INFN sez Genova)

Presenter: LAPERTOSA, Alessandro (INFN e Universita Genova (IT))

Session Classification: Session 11: 3D Sensors

Track Classification: 3D Sensors